E·XFL

NXP USA Inc. - MKV10Z128VLH7 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	75MHz
Connectivity	I ² C, SPI, UART/USART
Peripherals	DMA, LVD, POR, WDT
Number of I/O	54
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	·
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 2x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkv10z128vlh7

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Part Number	Memory		FlexCAN	Maximum number of	
	Flash (KB)	SRAM (KB)		I\O's	
MKV11Z128VLH7	128	16	Yes	54	
MKV11Z128VLF7	128	16	Yes	40	
MKV11Z128VLC7 ²	128	16	Yes	28	
MKV11Z128VFM7	128	16	Yes	28	
MKV11Z64VLH7	64	16	Yes	54	
MKV11Z64VLF7	64	16	Yes	40	
MKV11Z64VLC7 ²	64	16	Yes	28	
MKV11Z64VFM7	64	16	Yes	28	
MKV10Z64VLH7	64	16	No	54	
MKV10Z64VLF7	64	16	No	40	
MKV10Z64VLC7 ²	64	16	No	28	
MKV10Z64VFM7	128	16	No	28	
MKV10Z128VLH7	128	16	No	54	
MKV10Z128VLF7	128	16	No	40	
MKV10Z128VLC7 ²	128	16	No	28	
MKV10Z128VFM7	128	16	No	28	

Ordering Information¹

1. To confirm current availability of ordererable part numbers, go to http://www.freescale.com and perform a part number search.

2. The 32-pin LQFP package supporting this part number is not yet available, however it is included in a Package Your Way program for Kinetis MCUs. Please visit http://www.freescale.com/KPYW for more details.

Related Resources

Туре	Description
Selector Guide	The Freescale Solution Advisor is a web-based tool that features interactive application wizards and a dynamic product selector.
Product Brief	The Product Brief contains concise overview/summary information to enable quick evaluation of a device for design suitability.
Reference Manual	The Reference Manual contains a comprehensive description of the structure and function (operation) of a device.
Data Sheet	The Data Sheet includes electrical characteristics and signal connections.
Chip Errata	The chip mask set Errata provides additional or corrective information for a particular device mask set.
Package drawing	Package dimensions are provided in package drawings.



Symbol	Description	Min.	Max.	Unit
V _{DD}	Digital supply voltage	-0.3	3.8	V
I _{DD}	Digital supply current	—	120	mA
V _{IO}	Digital pin input voltage (except open drain pins)	-0.3	VDD + 0.3 ¹	V
	Open drain pins (PTC6 and PTC7)	-0.3	5.5	V
Ι _D	Instantaneous maximum current single pin limit (applies to all port pins)	-25	25	mA
V _{DDA}	Analog supply voltage	V _{DD} – 0.3	V _{DD} + 0.3	V

1. Maximum value of V_{IO} (except open drain pins) must be 3.8 V.

2 General

Electromagnetic compatibility (EMC) performance depends on the environment in which the MCU resides. Board design and layout, circuit topology choices, location, characteristics of external components, and MCU software operation play a significant role in EMC performance.

See the following applications notes available on freescale.com for guidelines on optimizing EMC performance.

- AN2321: Designing for Board Level Electromagnetic Compatibility
- AN1050: Designing for Electromagnetic Compatibility (EMC) with HCMOS Microcontrollers
- AN1263: Designing for Electromagnetic Compatibility with Single-Chip Microcontrollers
- AN2764: Improving the Transient Immunity Performance of Microcontroller-Based Applications
- AN1259: System Design and Layout Techniques for Noise Reduction in MCU-Based Systems

2.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.



2.2.3 Voltage and current operating behaviors Table 3. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V _{OH}	Output high voltage — Normal drive pad				
	All port pins, except PTC6 and PTC7	V _{DD} – 0.5	_	v	
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OH} = -5 mA	V _{DD} – 0.5	_	v	
	• $1.71 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}, \text{ I}_{\text{OH}} = -1.5 \text{ mA}$				
V _{OH}	Output high voltage — High drive pad				
	PTB0, PTB1, PTC3, PTC4, PTD4, PTD5, PTD6,	V _{DD} – 0.5	_	v	
	PTD7 pins	V _{DD} – 0.5	_	v	
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OH} = -18 mA				
	• $1.71 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}, \text{ I}_{\text{OH}} = -6 \text{ mA}$				
I _{OHT}	Output high current total for all ports	_	100	mA	
V _{OL}	Output low voltage — Normal drive pad				
	All port pins		0.5	v	
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OL} = 5 mA		0.5	v	
	• 1.71 V \leq V _{DD} \leq 2.7 V, I _{OL} = 1.5 mA				
V _{OL}	Output low voltage — High drive pad				
	PTB0, PTB1, PTC3, PTC4, PTD4, PTD5, PTD6,	_	0.5	v	
	PTD7 pins		0.5	v	
	• 2.7 V \leq V _{DD} \leq 3.6 V, I _{OL} = 18 mA				
	• $1.71 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}, \text{ I}_{\text{OL}} = 6 \text{ mA}$				
I _{OLT}	Output low current total for all ports	—	100	mA	
I _{IN}	Input leakage current (per pin) for full temperature range	-	1	μA	
I _{IN}	Input leakage current (per pin) at 25 °C	_	0.025	μA	1
I _{IN}	Input leakage current (total all pins) for full temperature range	-	41	μA	1
I _{OZ}	Hi-Z (off-state) leakage current (per pin)		1	μA	
R _{PU}	Internal pullup resistors	20	50	kΩ	2

1. Measured at $V_{DD} = 3.6 V$

2. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}



2.2.4 Power mode transition operating behaviors

All specifications except t_{POR} and VLLSx \rightarrow RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 75 MHz
- Bus and flash clock = 25 MHz
- FEI clock mode

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t _{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.8 V to execution of the first instruction across the operating temperature range of the chip.	_	_	300	μs	
	• VLLS0 → RUN	_	123	132	μs	
	• VLLS1 → RUN	_	123	132	μs	
	VLLS3 → RUN		67	72	μs	
	 VLPS → RUN 		4	5	μs	
	• STOP → RUN		4	5	μs	

Table 4. Power mode transition operating behaviors

2.2.5 KV11x Power consumption operating behaviors Table 5. KV11x power consumption operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I _{DDA}	Analog supply current	—	—	5	mA	1
I _{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash					Target IDD
	• at 1.8 V 50 MHz (25 MHz Bus)	_	5.3	6.2	mA	
	• at 3.0 V 50 MHz (25 MHz Bus)	_	5.4	6.3	mA	
	 at 1.8 V 75 MHz (25 MHz Bus) at 3.0 V 75 MHz (25 MHz Bus) 	_	7.2	8.3	mA	
		_	7.3	8.3	mA	
I _{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash					Target IDD

Table continues on the next page...



Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
I _{FTM}	FTM peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source configured for output compare generating 100Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents.							μA
	MCGIRCLK (4 MHz internal reference clock)	150	150	150	150	150	150	F
	OSCERCLK (4 MHz external crystal)	300	300	300	320	340	350	
I _{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx, LLS, or VLLSx mode.	45	45	45	45	45	45	μA
I _{ADC}	ADC peripheral adder combining the measured values at VDD and VDDA by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	366	366	366	366	366	366	μΑ
Iwdog	WDOG peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at 115200 baud rate. Includes selected clock source power consumption.							_
	MCGIRCLK (4 MHz internal reference clock)	66	66	66	66	66	66	μA
	OSCERCLK (4 MHz external crystal)	214	237	246	254	260	268	

Table 6. Low power mode peripheral adders — typical value (continued)

2.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE for run mode (except for 75 MHz which is in FEE mode), and BLPE for VLPR mode
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA



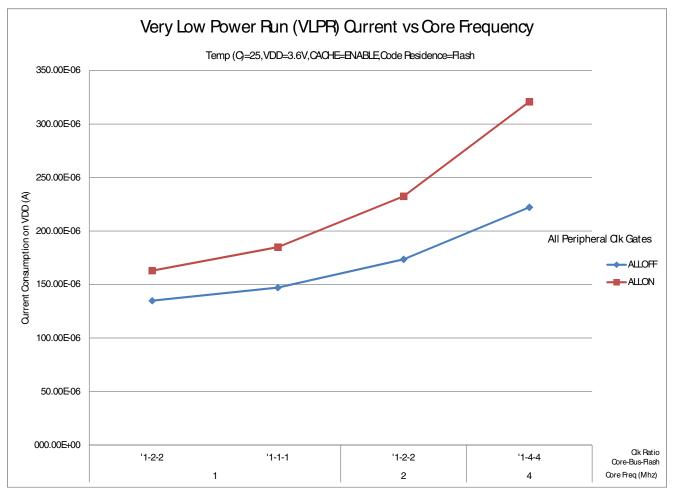


Figure 4. VLPR mode current vs. core frequency

2.2.6 EMC radiated emissions operating behaviors Table 7. EMC radiated emissions operating behaviors

Symbol	Description	Frequency band (MHz)	Тур.	Unit	Notes
V _{RE1}	Radiated emissions voltage, band 1	0.15–50	15	dBµV	1, 2
V _{RE2}	Radiated emissions voltage, band 2	50–150	17	dBµV	
V _{RE3}	Radiated emissions voltage, band 3	150–500	12	dBµV	
V _{RE4}	Radiated emissions voltage, band 4	500-1000	4	dBµV	
V _{RE_IEC}	IEC level	0.15–1000	М		2, 3

 Determined according to IEC Standard 61967-1, Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions and IEC Standard 61967-2, Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method. Measurements were made while the microcontroller was running basic application code.



Peripheral operating requirements and behaviors

- 2. Determined according to JEDEC Standard JESD51-8, Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board.
- 3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
- 4. Determined according to JEDEC Standard JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air).

3 Peripheral operating requirements and behaviors

3.1 Core modules

3.1.1 SWD Electricals

Table 13. SWD full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	SWD_CLK frequency of operation			
	Serial wire debug	0	25	MHz
J2	SWD_CLK cycle period	1/J1	_	ns
J3	SWD_CLK clock pulse width			
	Serial wire debug	20	_	ns
J4	SWD_CLK rise and fall times		3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	_	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	0	_	ns
J11	SWD_CLK high to SWD_DIO data valid	—	32	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	—	ns

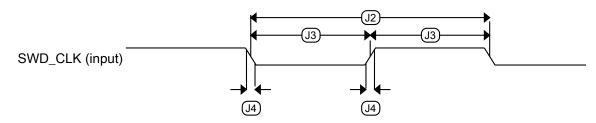
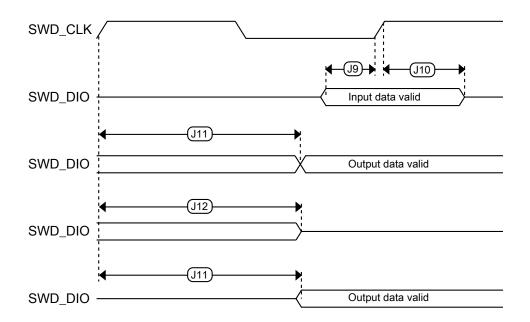


Figure 5. Serial wire clock input timing







3.2 System modules

There are no specifications necessary for the device's system modules.

3.3 Clock modules

3.3.1 MCG specifications

Table 14.	MCG	specifications
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Symbol	Description	Min.	Тур.	Max.	Unit	Notes
f _{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal V _{DD} and 25 °C	_	32.768	_	kHz	
f _{ints_t}	Internal reference frequency (slow clock) — user trimmed	31.25	_	39.0625	kHz	
$\Delta_{fdco_res_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM	_	± 0.3	± 0.6	%f _{dco}	1

Table continues on the next page...



Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t _{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t _{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	_	1000	_	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)		500		ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	_	0.6	_	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	_	1	_	ms	

 Table 16.
 Oscillator frequency specifications (continued)

- 1. Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.
- 2. When transitioning from FEI or FBI to FBE mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
- 3. Proper PC board layout procedures must be followed to achieve specifications.
- 4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

NOTE

The 32 kHz oscillator works in low power mode by default and cannot be moved into high power/gain mode.

3.4 Memories and memory interfaces

3.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

3.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t _{hvpgm4}	Longword Program high-voltage time	—	7.5	18	μs	_
t _{hversscr}	Sector Erase high-voltage time	—	13	113	ms	1
t _{hversall}	Erase All high-voltage time	—	52	452	ms	1

 Table 17.
 NVM program/erase timing specifications

1. Maximum time based on expectations at cycling end-of-life.



Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t _{rd1sec2k}	Read 1s Section execution time (flash sector)	—	—	60	μs	1
t _{pgmchk}	Program Check execution time	_	—	45	μs	1
t _{rdrsrc}	Read Resource execution time	_	—	30	μs	1
t _{pgm4}	Program Longword execution time		65	145	μs	_
t _{ersscr}	Erase Flash Sector execution time	_	14	114	ms	2
t _{rd1all}	Read 1s All Blocks execution time	_	—	0.9	ms	1
t _{rdonce}	Read Once execution time	_	—	30	μs	1
t _{pgmonce}	Program Once execution time	_	100	_	μs	
t _{ersall}	Erase All Blocks execution time	-	140	1150	ms	2
t _{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1

3.4.1.2 Flash timing specifications — commands Table 18. Flash command timing specifications

1. Assumes 25 MHz flash clock frequency.

2. Maximum times for erase parameters based on expectations at cycling end-of-life.

3.4.1.3 Flash high voltage current behaviors Table 19. Flash high voltage current behaviors

Symbol	Description	Min.	Тур.	Max.	Unit
I _{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	12.0	mA
I _{DD_ERS}			1.5	8.0	mA

3.4.1.4 Reliability specifications

Table 20. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
	Program	n Flash	-	-		
t _{nvmretp10k}	Data retention after up to 10 K cycles	5	50	—	years	—
t _{nvmretp1k}	Data retention after up to 1 K cycles	20	100	_	years	
n _{nvmcycp}	Cycling endurance	10 K	50 K		cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.

2. Cycling endurance represents number of program/erase cycles at -40 °C \leq T_i \leq 125 °C.



ADC electrical specifications

Symbol	Description	Conditions ¹ .	Min.	Typ. ²	Max.	Unit	Notes
		 Avg = 32 16-bit single-ended mode Avg = 32 	78	92	_	dB	
EIL	Input leakage error			I _{In} × R _{AS}		mV	I _{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	8
V _{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	8

Table 22. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$

Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

- The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
- 4. 1 LSB = $(V_{REFH} V_{REFL})/2^N$
- 5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
- 6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
- 7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.
- 8. ADC conversion clock < 3 MHz

Symbol	Description	Min.	Тур.	Max.	Unit
I _{DDHS}	Supply current, high-speed mode (EN = 1, PMODE = 1)	—	_	200	μΑ
I _{DDLS}	Supply current, low-speed mode (EN = 1, PMODE = 0)	_	_	20	μΑ
V _{AIN}	Analog input voltage	V _{SS}	_	V _{DD}	V
V _{AIO}	Analog input offset voltage	—	—	20	mV
V _H	Analog comparator hysteresis ¹				
	• CR0[HYSTCTR] = 00	—	5	_	mV
	 CR0[HYSTCTR] = 01 	_	10	_	mV
	• CR0[HYSTCTR] = 10	_	20	_	mV
	• CR0[HYSTCTR] = 11	_	30	_	mV
V _{CMPOh}	Output high	V _{DD} – 0.5	_	_	V
V _{CMPOI}	Output low			0.5	V
t _{DHS}	Propagation delay, high-speed mode (EN = 1, PMODE = 1)	20	35	200	ns
t _{DLS}	Propagation delay, low-speed mode (EN = 1, PMODE = 0)	80	100	600	ns
	Analog comparator initialization delay ²	_	_	40	μs
I _{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μA
INL	6-bit DAC integral non-linearity	-0.5	_	0.5	LSB ³
DNL	6-bit DAC differential non-linearity	-0.3	_	0.3	LSB

Table 23. Comparator and 6-bit DAC electrical specifications (continued)

1. Typical hysteresis is measured with input voltage range limited to 0.7 to V_{DD} – 0.7 V.

2. Comparator initialization delay is defined as the time between software writes to change control inputs (writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.

3. 1 LSB = $V_{reference}/64$



ADC electrical specifications

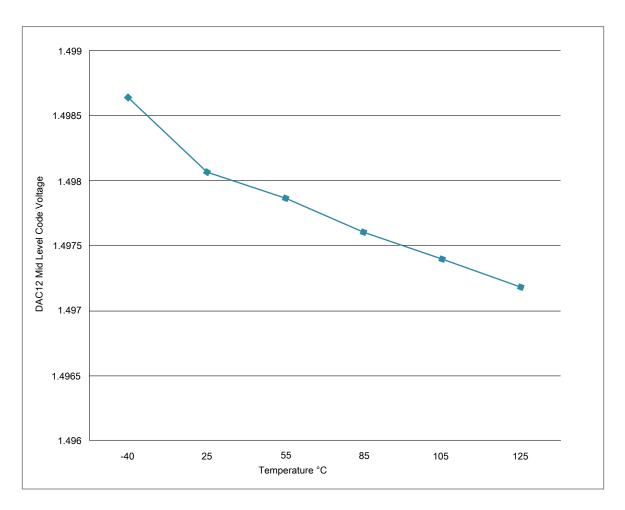


Figure 13. Offset at half scale vs. temperature

3.7 Timers

See General switching specifications.

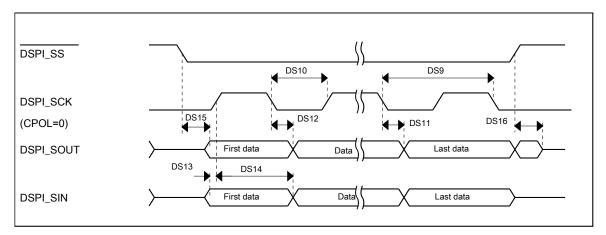
3.8 Communication interfaces

Symbol	Description	Min.	Max.	Unit	Notes
DS11	DSPI_SCK to DSPI_SOUT valid	_	27	ns	
DS12	DSPI_SCK to DSPI_SOUT invalid	0	_	ns	
DS13	DSPI_SIN to DSPI_SCK input setup	2.2	_	ns	
DS14	DSPI_SCK to DSPI_SIN input hold	7	_	ns	
DS15	DSPI_SS active to DSPI_SOUT driven	_	15	ns	
DS16	DSPI_SS inactive to DSPI_SOUT not driven	_	21	ns	
	Frequency of operation	_	18.75	MHz	4
DS9	DSPI_SCK input cycle time	4 x t _{BUS}		ns	2
DS10	DSPI_SCK input high/low time	(t _{SCK} /2) – 2	(t _{SCK} /2) + 2	ns	
DS11	DSPI_SCK to DSPI_SOUT valid	_	17	ns	
DS12	DSPI_SCK to DSPI_SOUT invalid	0	-	ns	
DS13	DSPI_SIN to DSPI_SCK input setup	2.2	_	ns	
DS14	DSPI_SCK to DSPI_SIN input hold	7	_	ns	
DS15	DSPI_SS active to DSPI_SOUT driven	-	15	ns	
DS16	DS16 DSPI_SS inactive to DSPI_SOUT not driven		11	ns	

1. Normal pads

- 2. The SPI module is clocked by the system clock
- 3. Open Drain pads: SIN: PTC7, SOUT:PTC6

4. Fast pads: SIN: PTD7, SOUT:PTD6, SCK: PTD5, PCS:PTD4







3.8.2 DSPI switching specifications (full voltage range)

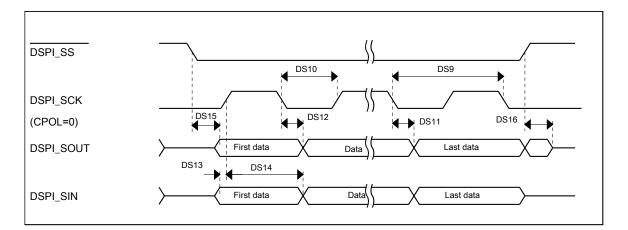
The DMA Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provides DSPI timing characteristics for classic SPI timing modes. Refer to the DSPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Symbol	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.7	3.6	V	1
	Frequency of operation	_	18.75	MHz	2
DS1	DSPI_SCK output cycle time	2 x t _{BUS}	-	ns	3
DS2	DSPI_SCK output high/low time	(t _{SCK} /2) – 4	(t _{SCK} /2) + 4	ns	
DS3	DSPI_PCS <i>n</i> valid to DSPI_SCK delay	(t _{SCK} /2) – 4	_	ns	4
DS4	DSPI_SCK to DSPI_PCSn invalid delay	(t _{SCK} /2) – 4	_	ns	5
DS5	DSPI_SCK to DSPI_SOUT valid	_	10		
DS6	DSPI_SCK to DSPI_SOUT invalid	-7.8	_	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	24	-	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	_	ns	
	Frequency of operation	-	18.75	MHz	6
DS1	DSPI_SCK output cycle time	2 x t _{BUS}	_	ns	3
DS2	DSPI_SCK output high/low time	(t _{SCK} /2) – 4	(t _{SCK} /2) + 4	ns	
DS3	DSPI_PCS <i>n</i> valid to DSPI_SCK delay	(t _{SCK} /2) – 4	-	ns	4
DS4	DSPI_SCK to DSPI_PCSn invalid delay	(t _{SCK} /2) – 4	-	ns	5
DS5	DSPI_SCK to DSPI_SOUT valid	_	26		
DS6	DSPI_SCK to DSPI_SOUT invalid	-7.8	-	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	24	-	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	_	ns	

Table 28. Master mode DSPI timing (full voltage range)

Table continues on the next page...







3.8.3 I²C

See General switching specifications.

3.8.4 UART

See General switching specifications.

4 Dimensions

4.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to www.freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
32-pin QFN	98ASA00473D
32-pin LQFP ¹	98ASH70029A
48-pin LQFP	98ASH00962A
64-pin LQFP	98ASS23234W

1. The 32-pin LQFP package for this product is not yet available, however it is included in a Package Your Way program for Kinetis MCUs. Please visit http://www.freescale.com/KPYW for more details.

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64 LQFP	48 QFP	32 QFN	32 LQFP	Pin Name	DEFAULT	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
14	10	_	—	VREFH	VREFH	VREFH							
15	11	-	-	VREFL	VREFL	VREFL							
16	12	-	-	VSSA	VSSA	VSSA							
17	13	-	-	PTE29	CMP1_IN5/ CMP0_IN5	CMP1_IN5/ CMP0_IN5	PTE29		FTM0_CH2		FTM_ CLKIN0		
18	14	9	9	PTE30	ADC1_SE4/ CMP1_IN4/ DAC0_OUT	ADC1_SE4/ CMP1_IN4/ DAC0_OUT	PTE30		FTM0_CH3		FTM_ CLKIN1		
19	-	-	-	PTE31	ADC0_SE14/ CMP0_IN4	ADC0_SE14/ CMP0_IN4	PTE31						
20	15	10	10	PTE24	DISABLED		PTE24	CAN0_TX	FTM0_CH0		I2C0_SCL	EWM_OUT_ b	
21	16	11	11	PTE25/ LLWU_P21	DISABLED		PTE25/ LLWU_P21	CAN0_RX	FTM0_CH1		I2C0_SDA	EWM_IN	
22	17	12	12	PTA0	SWD_CLK	SWD_CLK	PTA0	UARTO_ CTS_b	FTM0_CH5		EWM_IN		SWD_CLK
23	18	13	13	PTA1	DISABLED		PTA1	UART0_RX	FTM2_CH0	CMP0_OUT	FTM2_QD_ PHA	FTM1_CH1	FTM4_CH0
24	19	14	14	PTA2	DISABLED		PTA2	UART0_TX	FTM2_CH1	CMP1_OUT	FTM2_QD_ PHB	FTM1_CH0	FTM4_CH1
25	20	15	15	PTA3	SWD_DIO	SWD_DIO	PTA3	UART0_ RTS_b	FTM0_CH0	FTM2_FLT0	EWM_OUT_ b		SWD_DIO
26	21	16	16	PTA4/ LLWU_P3	NMI_b	NMI_b	PTA4/ LLWU_P3		FTM0_CH1	FTM4_FLT0	FTM0_FLT3		NMI_b
27	_	-	—	PTA5	DISABLED		PTA5		FTM0_CH2	FTM5_FLT0			
28	-	-	-	PTA12	DISABLED		PTA12	CAN0_TX	FTM1_CH0				FTM1_QD_ PHA
29	-	_	_	PTA13/ LLWU_P4	DISABLED		PTA13/ LLWU_P4	CAN0_RX	FTM1_CH1				FTM1_QD_ PHB
30	22	_	_	VDD	VDD	VDD							
31	23	-	—	VSS	VSS	VSS							
32	24	17	17	PTA18	EXTAL0	EXTAL0	PTA18		FTM0_FLT2	FTM_ CLKIN0		FTM3_CH2	
33	25	18	18	PTA19	XTAL0	XTAL0	PTA19	FTM0_FLT0	FTM1_FLT0	FTM_ CLKIN1		LPTMR0_ ALT1	
34	26	19	19	PTA20	RESET_b		PTA20						RESET_b
35	27	20	20	PTB0/ LLWU_P5	ADC0_SE8/ ADC1_SE8	ADC0_SE8/ ADC1_SE8	PTB0/ LLWU_P5	I2C0_SCL	FTM1_CH0			FTM1_QD_ PHA	UART0_RX
36	28	21	21	PTB1	ADC0_SE9/ ADC1_SE9	ADC0_SE9/ ADC1_SE9	PTB1	I2C0_SDA	FTM1_CH1	FTM0_FLT2	EWM_IN	FTM1_QD_ PHB	UART0_TX
37	29	_	-	PTB2	ADC0_SE10/ ADC1_SE10/ ADC1_DM2	ADC0_SE10/ ADC1_SE10/ ADC1_DM2	PTB2	I2C0_SCL	UART0_ RTS_b	FTM0_FLT1		FTM0_FLT3	
38	30	-	-	PTB3	ADC1_SE2/ ADC1_DP2	ADC1_SE2/ ADC1_DP2	PTB3	I2C0_SDA	UARTO_ CTS_b			FTM0_FLT0	



MKV11Z128VFM7

8 Terminology and guidelines

8.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

8.1.1 Example

This is an example of an operating requirement:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	0.9	1.1	V

8.2 Definition: Operating behavior

Unless otherwise specified, an *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

8.2.1 Example

This is an example of an operating behavior:

Symbol	Description	Min.	Max.	Unit
	Digital I/O weak pullup/ pulldown current	10	130	μΑ



8.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

8.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

8.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

- Operating ratings apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

8.4.1 Example

This is an example of an operating rating:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	-0.3	1.2	V



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